

## ABSTRACT

For semiconductor manufacturing equipment a ceramic susceptor is made available in which the temperature uniformity in the surface of a wafer during heating operations is enhanced by keeping fluctuations in the shape of the susceptor—particularly in the outer diameter along the thickness at normal temperature—under control.

The ceramic susceptor (1) for semiconductor manufacturing equipment has a resistive heating element (3) on a surface of or inside ceramic substrates (2a), (2b). The difference between the maximum outer diameter and minimum outer diameter along the thickness of the ceramic susceptor when not heating is 0.8% or less of the average diameter along the wafer-support side. A plasma electrode may be arranged on a surface of or inside the ceramic substrates (2a), (2b) of the ceramic susceptor (1). The ceramic substrates (2a), (2b) are preferably made of at least one selected from aluminum nitride, silicon nitride, aluminum oxynitride, and silicon carbide.